

131,072 x 8 CMOS EPROM

NOVEMBER 1997

FEATURES

- · Fast read access time: 90 ns
- JEDEC-approved pinout
- High-speed write programming
 Typically less than 16 seconds
- 5V ±10% power supply tolerance available
- Both CMOS and TTL compatible input and output
- · Two line control functions
- Industrial and commercial temperature ranges available

DESCRIPTION

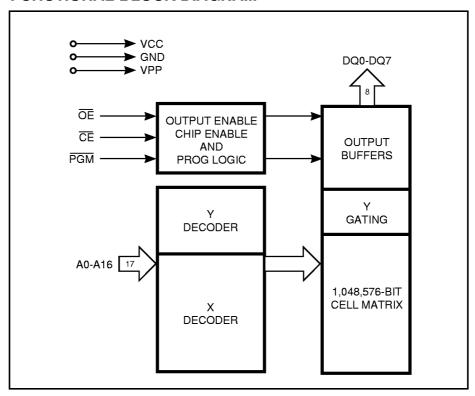
The ISSI IS27C010 is a 1 megabit (128K-word by 8-bit) CMOS Programmable Read-Only Memory. It requires only a single 5V power supply in normal read mode operation. Any byte can be accessed in less than 90 ns. The IS27C010 offers separate Output Enable (\overline{OE}) and Chip Enable (\overline{CE}) controls, thus eliminating bus contention in a multiple bus microprocessor system.

All signals are TTL levels, including programming signals. Bit locations may be programmed singly, in blocks, or at random.

The IS27C010 uses ISSI's write programming algorithm. Programming time is typically only 100 μ s per byte.

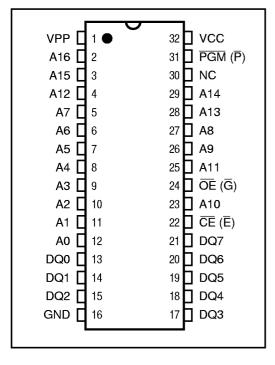
This product is available in One-Time Programmble (OTP) PDIP, PLCC, and TSOP packages over commercial and industrial temperature ranges.

FUNCTIONAL BLOCK DIAGRAM



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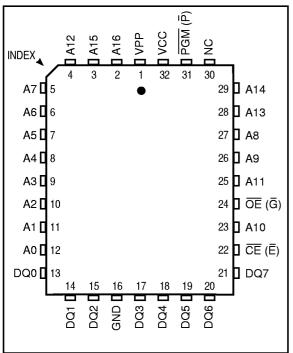
PIN CONFIGURATIONS 32-Pin DIP



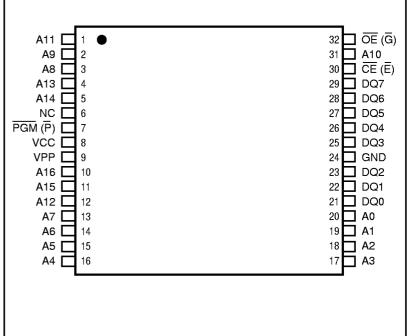
PIN DESCRIPTIONS

A0-A16	Address Inputs	
CE (E)	Chip Enable Input	
DQ0-DQ7	Data Inputs/Outputs	
ŌĒ (G)	Output Enable Input	
PGM (P)	Program Enable Input	
Vcc	Power Supply Voltage	
V PP	Program Supply Voltage	
GND	Ground	
NC	No Internal Connection	

32-Pin PLCC



32-Pin TSOP



FUNCTIONAL DESCRIPTION

Programming the IS27C010

Upon delivery, the IS27C010 has 1,048,576 bits in the "ONE", or HIGH state. "ZEROs" are loaded into the IS27C010 through the procedure of programming.

The programming mode is entered when 12.5 \pm 0.25V is applied to the VPP pin, \overline{CE} and \overline{PGM} is at VIL, and \overline{OE} is at VIH. For programming, the data to be programmed is applied eight bits in parallel to the data output pins.

The write programming algorithm reduces programming time by using 100 μs programming pulses followed by a byte verification to determine whether the byte has been successfully programmed. If the data does not verify, an additional pulse is applied for a maximum of 25 pulses. This process is repeated while sequencing through each address of the EPROM.

The write programming algorithm programs and verifies at Vcc = 6V and Vpp = 12.5V. After the final address is completed, all byte are compared to the original data with Vcc = 5.25V.

Program Inhibit

Programming of multiple IS27C010s in parallel with different data is also easily accomplished. Except for \overline{CE} , all like inputs of the parallel IS27C010 may be common. A TTL low-level program pulse applied to an IS27C010 \overline{CE} input with VPP = 12.5 \pm 0.25V, \overline{PGM} LOW and \overline{OE} HIGH will program that IS27C010. A high-level \overline{CE} input inhibits the other IS27C010 from being programmed.

Program Verify

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify should be performed with \overline{OE} and \overline{CE} at V_{IL} , \overline{PGM} at V_{IH} , and V_{PP} between 12.25V and 12.75V.

Auto Select Mode

The auto select mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C \pm 5°C ambient temperature range that is required when programming the IS27C010.

To activate this mode, the programming equipment must force $12.0\pm0.5V$ on address line A9 of the IS27C010. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from VIL to VIH. All other address lines must be held at VIL during auto select mode.

Byte 0 (A0 = V_{IL}) represents the manufacturer code, and byte 1 (A0 = V_{IH}), the device identifier code. For the IS27C010, these two identifier bytes are given in the Mode Select table. All identifiers manufacturer and device codes will possess odd parity, with the MSB (DQ7) defined as the parity bit.

Read Mode

The IS27C010 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (\overline{CE}) is the power control and should be used for device selection. Assuming that addresses are stable, address access time (tacc) is equal to the delay from \overline{CE} to output (tce). Output Enable (\overline{OE}) is the output control and should be used to get data to the output pins, independent of device selection. Data is available at the outputs toe after the falling edge of \overline{OE} assuming that \overline{CE} has been LOW and addresses have been stable for at least tacc – toe.

Standby Mode

The IS27C010 is placed in CMOS standby mode when \overline{CE} is at Vcc \pm 0.3V and in TTL standby mode when \overline{CE} is at Vih. When in standby mode, the outputs are in a high-impedance state, independent of the \overline{OE} input.

Output OR-Tieing

To accommodate multiple memory connections, a twoline control function is provided to allow for:

- 1. Low memory power dissipation, and
- 2. Assurance that output bus contention will not occur.

It is recommended that \overline{CE} be decoded and used as the primary device-selecting function, while \overline{OE} be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in their low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

System Applications

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device at a minimum, a 0.1 μF ceramic capacitor (high-frequency, low inherent inductance) should be used on each device between Vcc and GND to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on EPROM arrays, a 4.7 μF bulk electrolytic capacitor should be used between Vcc and GND for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

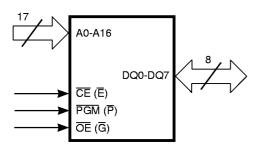
TRUTH TABLE(1,2)

Mode	CE	ŌĒ	PGM	Α0	A9	Vpp	Outputs
Read	VIL	VIL	Х	Х	Х	Vcc	D ouт
Output Disable	VıL	Vін	Х	Х	Х	Vcc	Hi-Z
Standby	ViH	Х	Х	Х	Х	Vcc	Hi-Z
Program	VIL	Vін	VıL	Х	Х	V PP	Din
Program Verify	VıL	VıL	Vін	Х	Х	V PP	D out
Program Inhibit	ViH	Х	Х	Х	Х	VPP	Hi-Z
Auto Select ⁽³⁾ Manufacturer Co	de Vı∟	VıL	Χ	VIL	Vн	Vcc	D5H
Device Co	de Vı∟	Vı∟	Χ	Vін	Vн	Vcc	0EH

Notes:

- 1. $V_H = 12.0V \pm 0.5V$.
- 2. $X = Either V \vdash Or V \vdash C$
- 3. A1-A8 = A10-A16 = V_IL.
- 4. See DC Programming Characteristics for VPP voltage during programming.

LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit
VTERM	Terminal Voltage with Respect to GND		
	All pins except A9 and VPP	-0.6 to Vcc + $0.5^{(2)}$	V
	VPP	$Vcc - 0.3$ to $13.5^{(2,3)}$	V
	A9	-0.6 to $13.5^{(2,3)}$	V
	Vcc	-0.6 to 7.0 ⁽²⁾	V
Та	Ambient Temperature with Power Applied	-65 to +125	°C
Тѕтс	Storage Temperature (OTP)	-65 to +125	°C
Тѕтс	Storage Temperature (All others)	-65 to +150	°C

Notes:

- Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the
 device. This is a stress rating only and functional operation of the device at these or any other conditions above
 those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum
 rating conditions for extended periods may affect reliability.
- Minimum DC input voltage is -0.5V. During transitions, inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is Vcc + 0.5V which may overshoot to Vcc + 2.0V for periods less than 10 ns.
- 3. Maximum DC voltage on A9 or VPP may overshoot to +13.5V for periods less than 10 ns.

OPERATING RANGE

Range	Ambient Temperature	Vcc
Commercial	0°C to +70°C	5V ± 10%
Industrial ⁽¹⁾	–40°C to +85°C	5V ± 10%

Note:

1. Operating ranges define those limits between which the functionally of the device is guaranteed.

DC ELECTRICAL CHARACTERISTICS(1,2,3) (Over Operating Range)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Vон	Output HIGH Voltage	$Vcc = Min., IoH = -400 \mu A$	2.4	_	V
Vol	Output LOW Voltage	Vcc = Min., loL = 2.1 mA	_	0.45	V
VIH	Input HIGH Voltage(4)		2.0	Vcc + 0.5	V
VIL	Input LOW Voltage(4)		-0.3	0.8	٧
lu	Input Load Current	VIN = 0V to +Vcc		10	μA
llo	Output Leakage Current	Vout = 0V to +Vcc	_	10	μΑ

- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP. Never try to force VPP LOW to 1V below Vcc. Manufacturer suggests to tie VPP and Vcc together during the READ operation.
- 2. Caution: the IS27C010 must not be removed from (or inserted into) a socket when Vcc or VPP is applied.
- 3. Minimum DC input voltage is -0.5V. During transitions, the inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is Vcc + 0.5V which may overshoot to Vcc + 2.0V for periods less than 10 ns.
- 4. Tested under static DC conditions.

POWER SUPPLY CHARACTERISTICS(1,2,5) (Over Operating Range)

Symbol	Parameter	Test Conditions		Min.	Max.	Unit
lcc1	Vcc Operating Supply Current ⁽³⁾	Vcc = Max., \overline{CE} = VIL Colour = 0 mA, f = 5 MHz	ommercial Industrial	_	30 40	mA
lpp1	VPP Current During Read ⁽⁴⁾	$V_{CC} = Max., \overline{CE} = \overline{OE} = V_{IL}$ $V_{PP} = V_{CC}$		_	100	μА
Iccsb0	Vcc CMOS Standby Current	CE ≥ Vcc – 0.3V		_	50	μΑ
IccsB1	Vcc TTL Standby Current	CE ≥ Viн Other Inputs = Viн or Vi∟ (TTL Le	evel)	_	1	mA

Notes:

- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP. Never try to force VPP LOW to 1V below Vcc. Manufacturer suggests to tie VPP and Vcc together during the READ operation.
- 2. Caution: the IS27C010 must not be removed from (or inserted into) a socket when Vcc or VPP is applied.
- 3. Icc1 is tested with $\overline{OE} = V_{H}$ to simulate open outputs.
- 4. Maximum active power usage is the sum of Icc and IPP.
- 5. Minimum DC input voltage is -0.5V. During transitions, the inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is Vcc + 0.5V which may overshoot to Vcc + 2.0V for periods less than 10 ns.

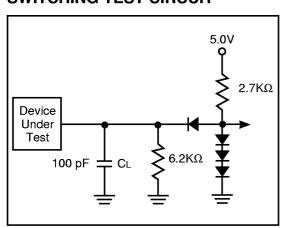
CAPACITANCE(1,2,3)

Symbol	Parameter	Conditions	Тур.	Max.	Unit
Cin	Input Capacitance	VIN = 0V	7	10	рF
Соит	Output Capacitance	Vout = 0V	8	12	pF

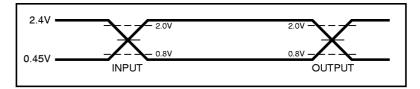
Notes:

- 1. Typical values are for nominal supply voltage.
- 2. This parameter is only sampled, but not 100% tested.
- 3. Test conditions: TA = 25°C, f = 1 MHz.

SWITCHING TEST CIRCUIT



SWITCHING TEST WAVEFORM



Notes:

AC Testing:

- 1. Inputs are driven at 2.4V for a logic "1" and 0.45V for a logic "0".
- 2. Input pulse rise and fall times are < 20 ns.

SWITCHING CHARACTERISTICS(1,2,3,4) (Over Operating Range)

JEDEC	Std.			-(90	-1	12		15	
Symbol	Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tavqa	tacc	Address to Output Delay	CE = OE = VIL	_	90	_	120	_	150	ns
t ELQ V	t ce	Chip Enable to Output Delay	ŌĒ = VIL	_	90	_	120	_	150	ns
tglqv	t oe	Output Enable to Output Delay	CE = VIL	_	45	_	50	_	65	ns
tehoz, tghqz	t _{DF} ⁽²⁾	Chip Enable HIGH or Output Enable HIGH, whichever comes first, to Output Float		_	30	_	35	_	35	ns
tavox	tон	Output Hold from Address, CE or OE whichever occured first		0	_	0	_	0	_	ns

Notes:

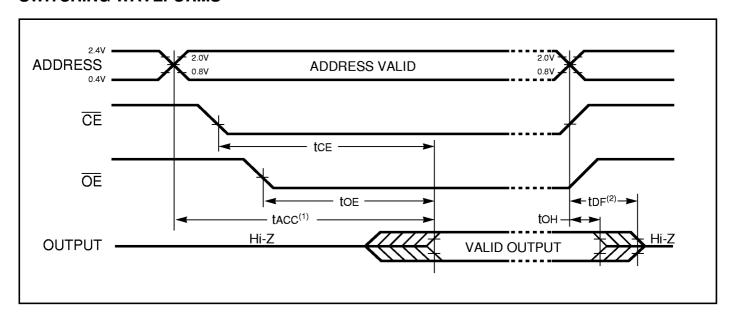
- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP.
- 2. This parameter is only sampled, not 100% tested.
- 3. Caution: The IS27C010 must not be removed from (or inserted into) a socket or board when VPP or Vcc applied.
- 4. Output Load: 1 TTL gate and $C_L = 100 \text{ pF}$.

Input Rise and Fall times: 20 ns.

Input Pulse Levels: 0.45V to 2.4V.

Timing Measurement Reference Level: 0.8V to 2V for inputs and outputs.

SWITCHING WAVEFORMS



- 1. \overline{OE} may be delayed \underline{up} to \underline{tacc} toe after the falling edge of \overline{CE} without impact on tacc. 2. \underline{toe} is specified from \overline{OE} or \overline{CE} , whichever occurs first.

DC PROGRAMMING CHARACTERISTICS^(1,2,3,4) (TA = +25°C ± 5 °C)

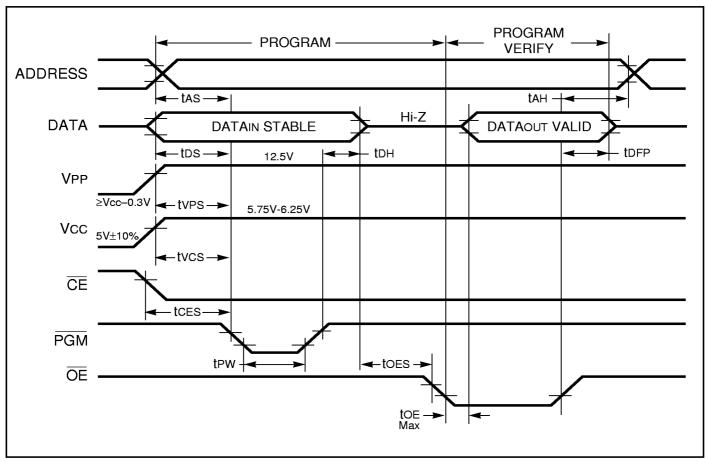
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
V он	Output HIGH Voltage During Verify	Ioн = -400 μA	2.4	_	V
V OL	Output LOW Voltage During Verify	IoL = 2.1 mA		0.45	V
VIH	Input HIGH Voltage		2.0	Vcc + 0.5	V
VIL	Input LOW Voltage (All Inputs)		-0.3	8.0	V
VH	A9 Auto Select Voltage		11.5	12.5	V
lu	Input Current (All Inputs)	VIN = VIL Or VIH	_	1	μΑ
lcc	Vcc Supply Current (Program & Verify)		_	50	mA
I PP	VPP Supply Current	CE = VIL, OE = VIH	_	30	mA
Vcc	Supply Voltage		5.75	6.25	V
V PP	Programming Voltage		12.25	12.75	V

SWITCH PROGRAMMING CHARACTERISTICS(1,2,3,4) (TA = +25°C \pm 5°C)

JEDEC Symbol	Std. Symbol	Parameter	Min.	Max.	Unit
tavel	tas	Address Setup Time	2		μs
t DZGL	toes	OE Setup Time	2	_	 μs
t DVEL	t DS	Data Setup Time	2		μs
t GHAX	t ah	Address Hold Time	0	_	μѕ
t EHDX	t dh	Data Hold Time	2	_	μs
t gHQZ	t DFP	OE to Output Float Delay	0	130	ns
t vps	t vps	VPP Setup Time	2	_	μs
t ELEH1	tpw	PGM Program Pulse Width	95	105	μs
tvcs	tvcs	Vcc Setup Time	2	_	μs
t ELPL	tces	CE Setup Time	2	_	μs
t GLQV	t oe	Data Valid from OE	_	150	ns

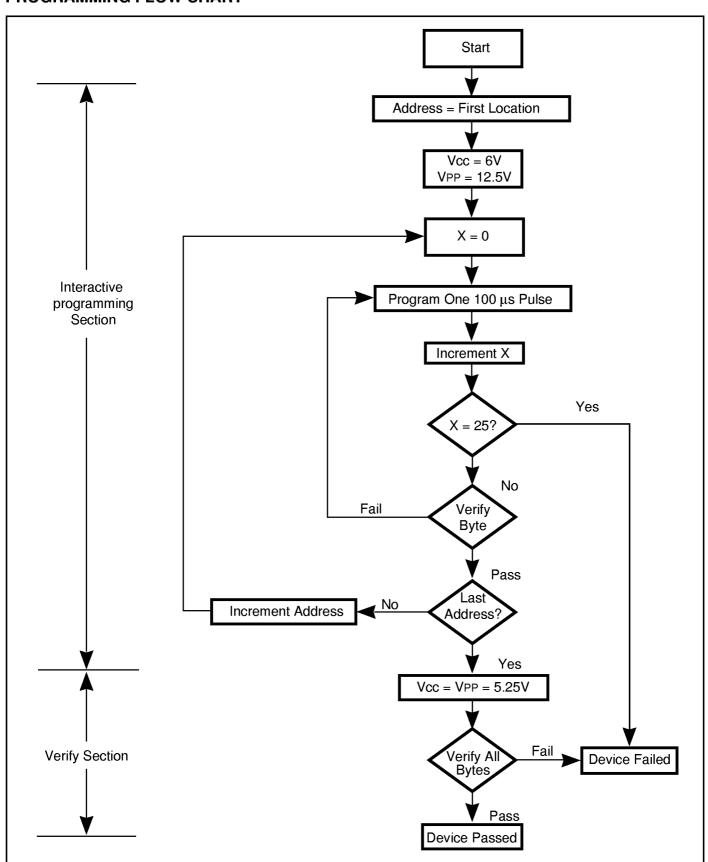
- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP.
- VPP must be ≥ Vcc during the entire programming and verifying procedure.
 When programming IS27C010, a 0.1 μF capacitor is required across VPP and ground to suppress spurious voltage transients which may damage the device.
- 4. Programming characteristics are sampled but not 100% tested at worst-case conditions.

PROGRAMMING ALGORITHM WAVEFORM(1,2)



- The timing reference level is 0.8V to 2V for inputs and outputs.
- toe and toff are characteristics of the device but must be accommodated by the programmer.

PROGRAMMING FLOW CHART



ORDERING INFORMATION

Commerical Range: 0°C to +70°C

Speed (ns)	Order Part Number	Package
90	IS27C010-90W IS27C010-90PL IS27C010-90T	600-mil Plastic DIP PLCC – Plastic Leaded Chip Carrier TSOP
120	IS27C010-12W IS27C010-12PL IS27C010-12T	600-mil Plastic DIP PLCC – Plastic Leaded Chip Carrier TSOP
150	IS27C010-15W IS27C010-15PL IS27C010-15T	600-mil Plastic DIP PLCC – Plastic Leaded Chip Carrier TSOP

ORDERING INFORMATION

Industrial Range: -40°C to +85°C

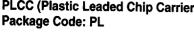
Speed (ns)	Order Part Number	Package
90	IS27C010-90PLI IS27C010-90TI	PLCC – Plastic Leaded Chip Carrier TSOP
120	IS27C010-12PLI IS27C010-12TI	PLCC – Plastic Leaded Chip Carrier TSOP
150	IS27C010-15PLI IS27C010-15TI	PLCC – Plastic Leaded Chip Carrier TSOP

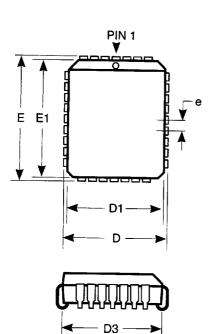


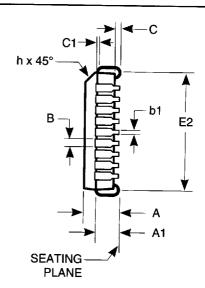
Integrated Silicon Solution, Inc.

2231 Lawson Lane Santa Clara, CA 95054 Fax: (408) 588-0806 Toll Free: 1-800-379-4774

http://www.issiusa.com







Plasstic Leaded Chip Carrier (PL)									
Inches									
Symbol	Min	Max	Min	Max					
Ref. Std.									
No. Leads	32		44						
A	0.131	0.140	0.165	0.180					
A1	0.075	0.095	0.090	0.120					
В	0.026	0.032	0.026	0.032					
b1	0.013	0.021	0.013	0.021					
С	0.020	0.040	0.020	0.040					
C1	0.008	0.014	0.008	0.014					
D	0.485	0.495	0.685	0.695					
D1	0.447	0.453	0.650	0.656					
D2	0.390	0.430	_						
E	0.585	0.595	0.685	0.695					
E1	0.547	0.553	0.650	0.656					
E2	0.490	0.530	0.659	0.680					
е	0.050	BSC	0.050 BSC						

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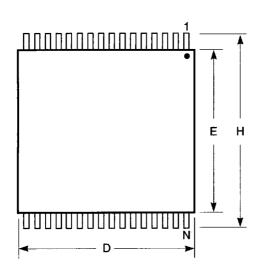
Notes:

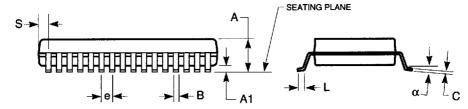
- 1. Controlling dimension: inches, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- 3. Dimensions D and E do not include mold flash protrusions.
- 4. Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.
- ND and NE represent the number of leads in D and E directions, respectively.
- 6. D1 and E1 should be measured from the bottom of the package.

7/9

ND/NE

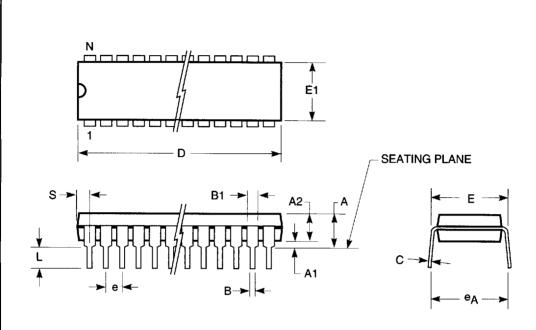
Plastic TSOP - 32 pins Package Code: T





Plastic TSOP (T)							
Inches							
Symbol	Min	Max					
Ref. Std.							
N	3.	2					
Α		0.047					
A1	0.002	0.010					
В	0.007	0.009					
С	0.006	0.014					
D	0.311	0.319					
Е	0.720	0.728					
H	0.780	0.795					
е	0.020	BSC					
L	0.016	0.025					
α	0°	8°					

- 1. Controlling dimension: inches, unless otherwise specified.
- BSC = Basic lead spacing between centers.
- Dimensions D and E do not include mold flash protrusions and should be measured from the bottom of the package.
- Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.



600-mil Plastic DIP (W)										
Inches										
Symbol	Min	Max	Min	Max	Min	Max				
Ref. Std.										
N	28		3	32		40				
Α	0.160	0.185	0.165	0.180	0.165	0.200				
A1	0.015	0.035	0.010		0.020	0.045				
В	0.015	0.020	0.0	18	0.015	0.022				
B1	0.050	0.065	0.0	50	0.045	0.067				
С	800.0	0.012	0.0	110	0.008	0.015				
D	1.420	1.460	1.645	1.655	1.415	1.460				
Е	0.600	0.620	0.590	0.610	0.600	0.620				
E1	0.530	0.550	0.540	0.555	0.530	0.560				
e _A	0.610	0.670	0.620	0.680	0.600	0.680				
е	0.100 BSC		0.100	0.100 BSC		0.100 BSC				
L	0.120	0.150	0.120	0.140	0.120	0.138				
S	0.055	0.080	0.065	0.085	0.055	0.085				
α	0°	15°	2°	8°						

- 1. Controlling dimension: inches, unless otherwise specified.
- BSC = Basic lead spacing between centers.
- Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
- Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.